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CERTIFICATE OF MAILING

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Tanya Parker

(Typed or Printed Name of Person Mailing Paper or Fee)

Technology Center 2100

(Signature of Person Mailing Paper or Fee)

Attorney Docket No.: NMTC-0770

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Inventor:

Kevin D. MacLean, et al.

Title:

USING SUGGESTED A SOLUTION TO SPEED UP A PROCESS FOR

SIMULATING AND CORRECTING AN INTEGRATED CIRCUIT LAYOUT

Filing Date:

March 15, 2002

Serial Number:

10/098,714

Group Art Unit:

2123

Examiner:

To Be Assigned

Listed below or on an attached Form PTO-1449 is information known to applicant(s) and submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication and U.S. and foreign patent, except for pending U.S. applications, is being submitted herewith, along with a concise explanation of information in a foreign language, if any, pursuant to 37 C.F.R. §1.97-1.98.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP §609.

This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in §1.56.

 \underline{X} This statement qualifies under 37 C.F.R. §1.97, subsection (b) because (check all that apply):

- (1) It is being filed within 3 months of the application filing date
- __ (2) It is being filed within 3 months of entry of a national stage
- X (3) It is being filed before the mail date of the first Office Action on the merits.

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	filing d set fort merits,	$C.R. \S 1.97(c)$. If this statement is being filed after the latest of: (1) three months beyond the late of a national application; (2) three months beyond the date of entry of the national stage as h in $\S 1.491$ in an international application; or (3) the mailing date of a first Office action on the but before the mailing date of the earlier of a final office action under $\S 1.113$ or a notice of nee under $\S 1.311$, then:
	_	a certification as specified in §1.97(e) is provided below; or
	_	a fee of \$240.00 as set forth in §1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement. Please note that a check in the amount of \$240.00 is enclosed in payment.
_		$R. \S 1.97(d)$. If this statement is being filed after the mailing date of the earlier of a final office under $\S 1.113$ or a notice of allowance under $\S 1.311$, but before payment of the issue fee, then:
	A.	a certification as specified in §1.97(e) is completed below; and
	B.	a petition under 37 C.F.R. §1.97(d) requesting consideration of this statement is submitted herewith; and
	C.	a fee of \$130.00 as set forth in §1.17(i)(1) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
_	patent of filing of information information after mestatement	ent under 37 C.F.R. §1.97(e) - I hereby certify that either: each item of information need in the information disclosure statement was cited in a communication from a foreign office in a counterpart foreign patent application not more than three months prior to the of the information disclosure statement; or no item of information contained in the ation disclosure statement was cited in a communication from a foreign patent office in a repart foreign patent application, and, to the knowledge of the person signing the statement aking reasonable inquiry, no item of information contained in the information disclosure ent was known to any individual designated in section 1.56(c) more than three months prior filing of the information disclosure statement.
	Signati	A. Richard Park (Reg. No. 41,241) Date
		Respectfully submitted,

By: A. Richard Park
Reg. No. 41,241

PARK, VAUGHAN & FLEMING LLP 508 Second Street, Suite 201 Davis, CA 95616 (530) 759-1661

Date: July 17, 2002

INFORMATION DISCLOSURE **CITATION**

PTO-1449

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Applicant

MACLEAN, Kevin

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